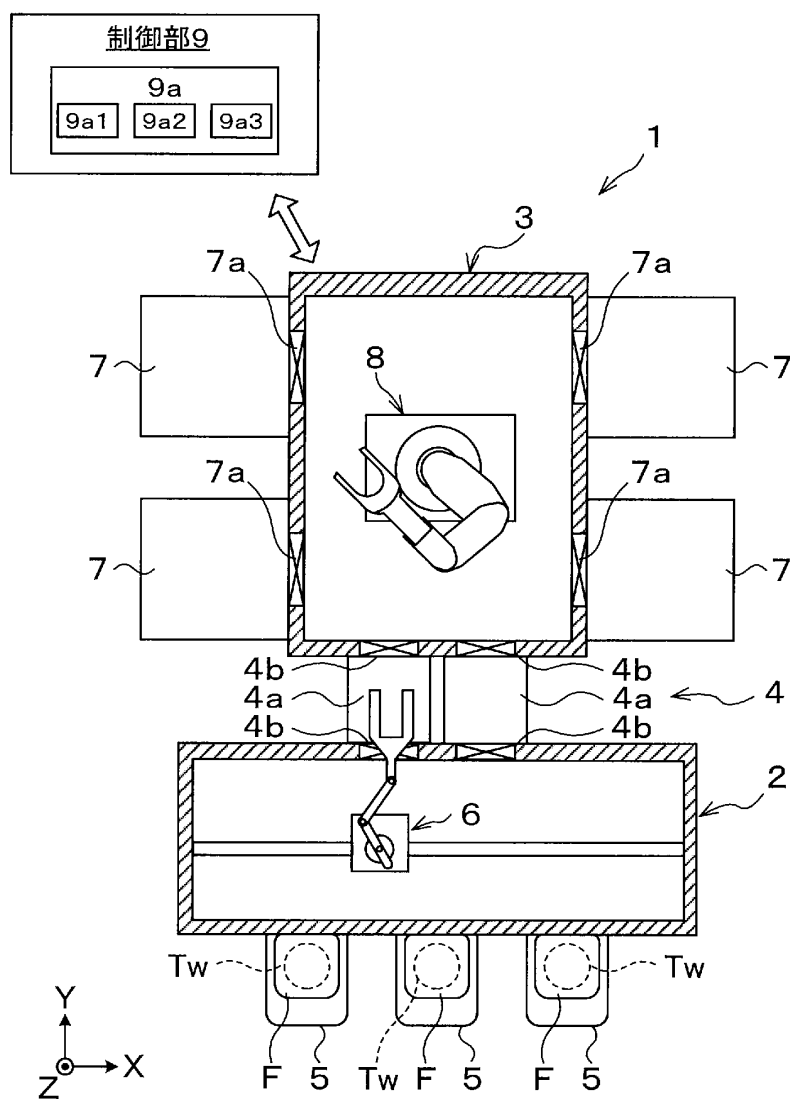
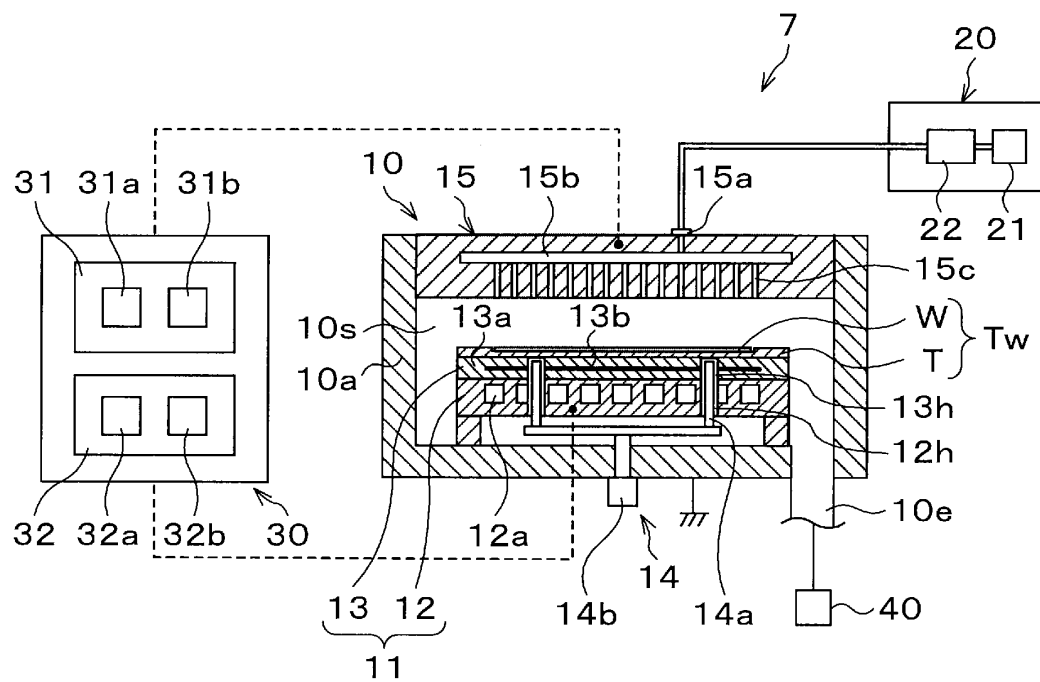
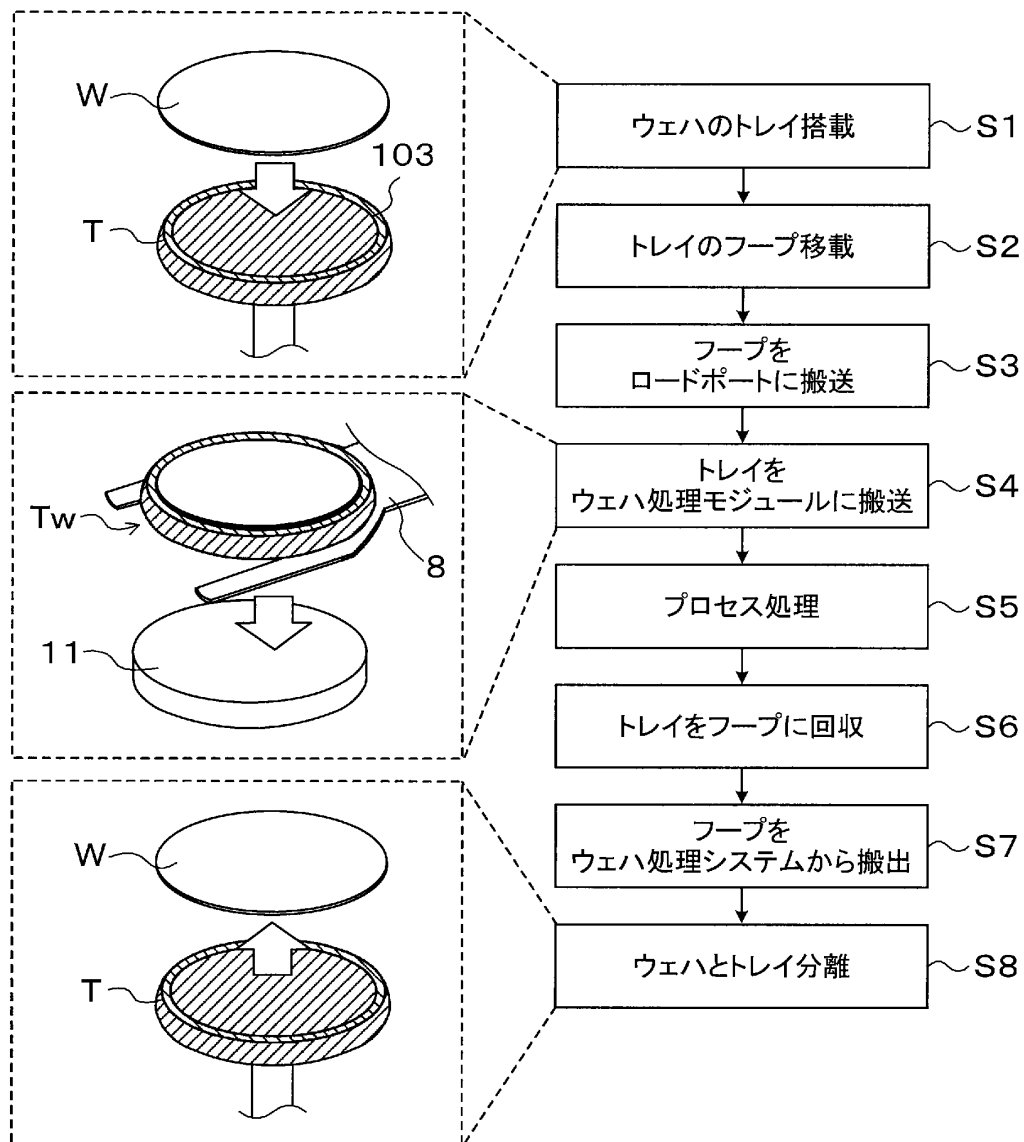


[図1]

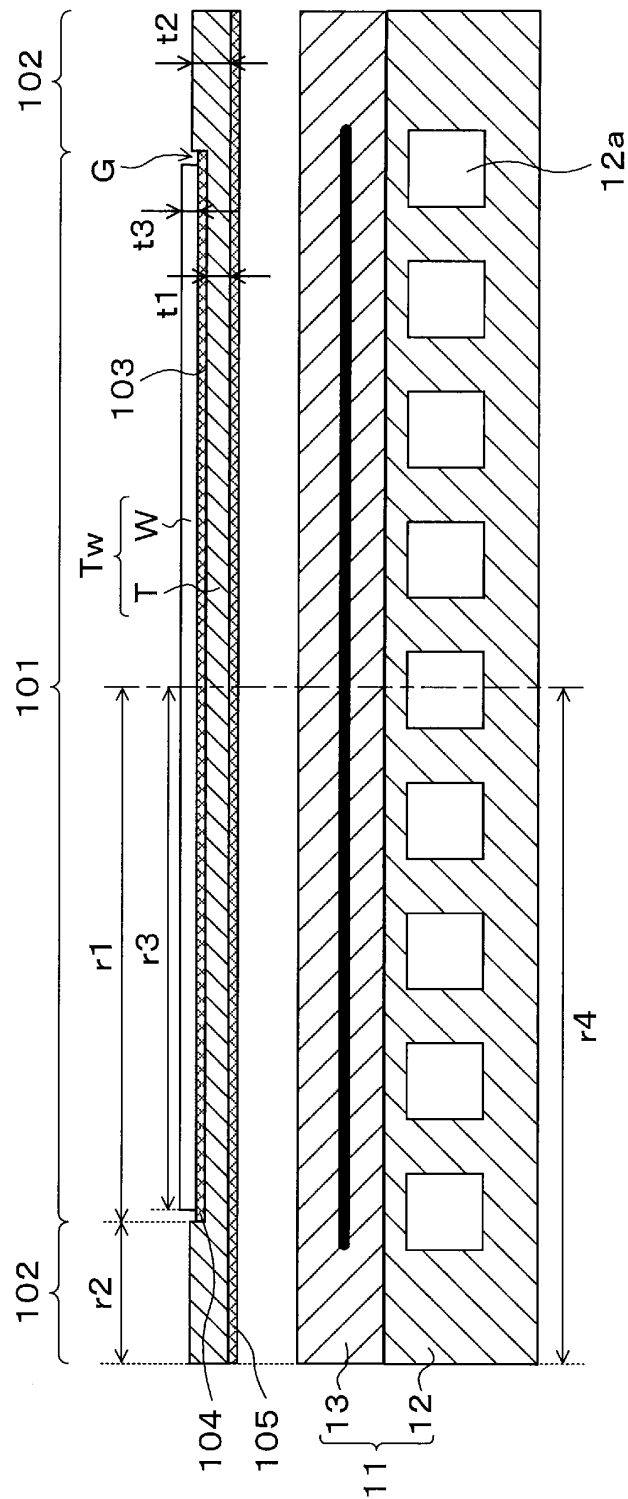




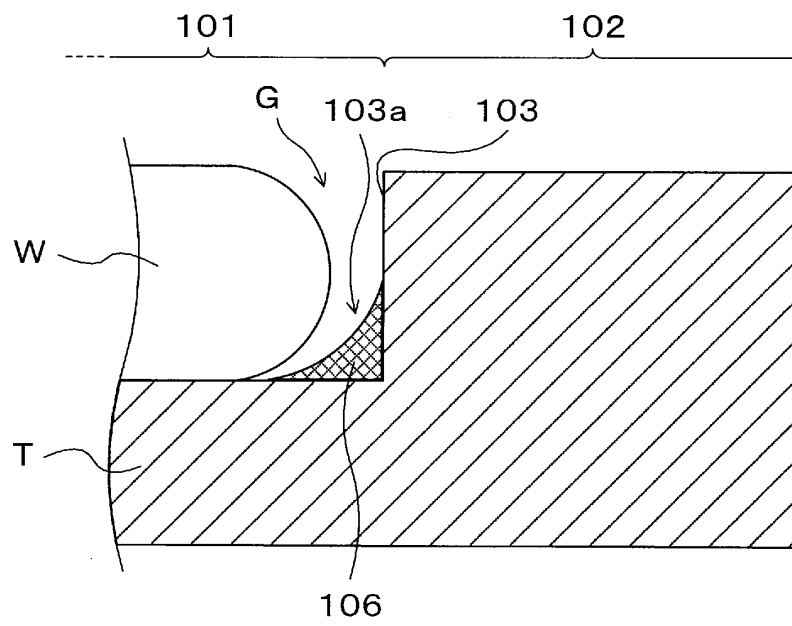
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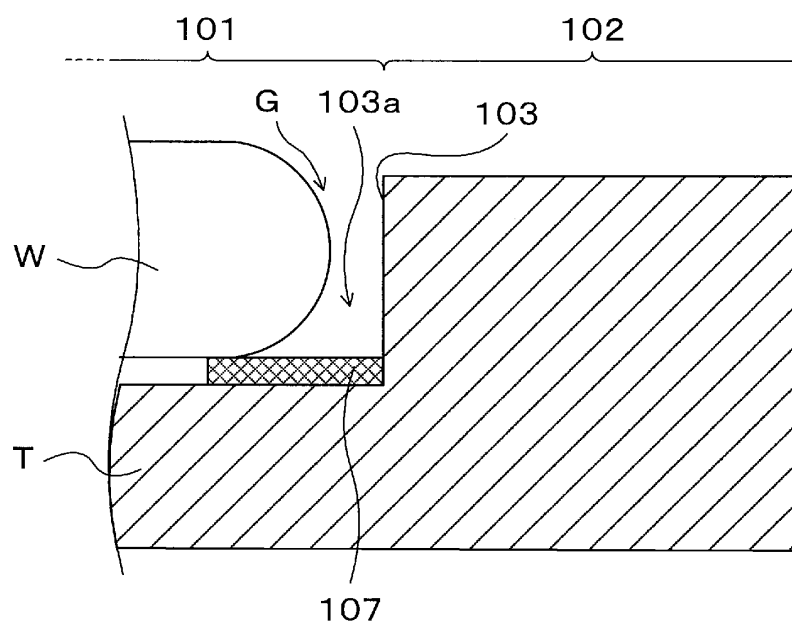
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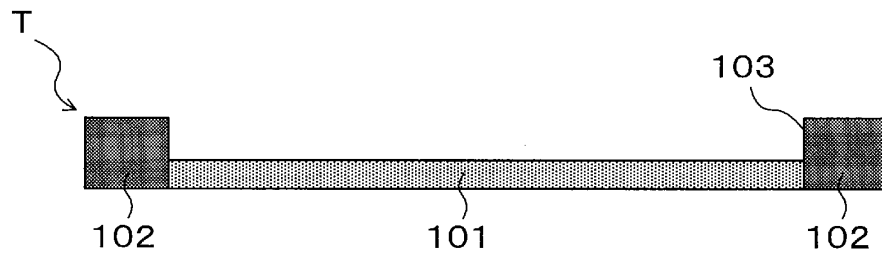
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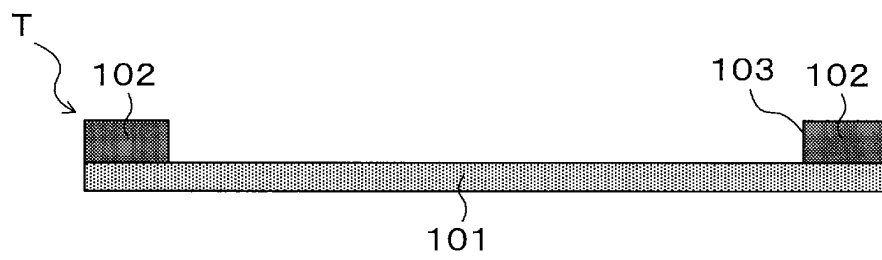
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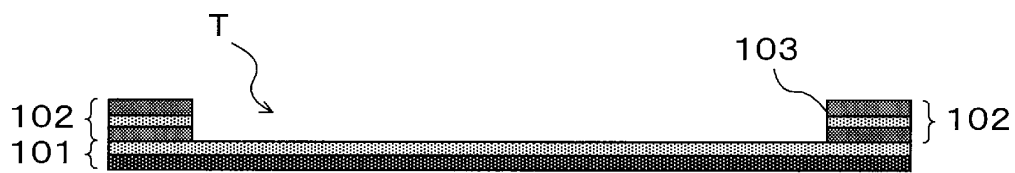
[図7]



[図8]



[図9]



[図10]

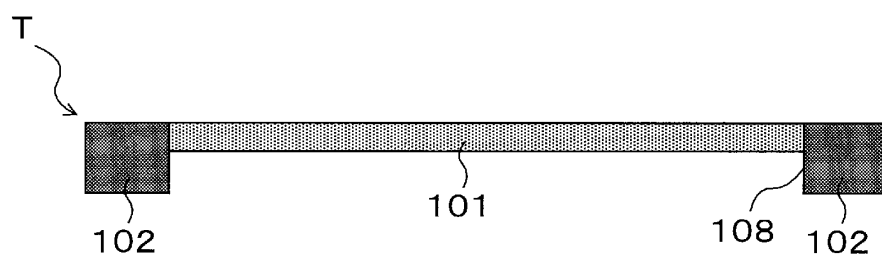
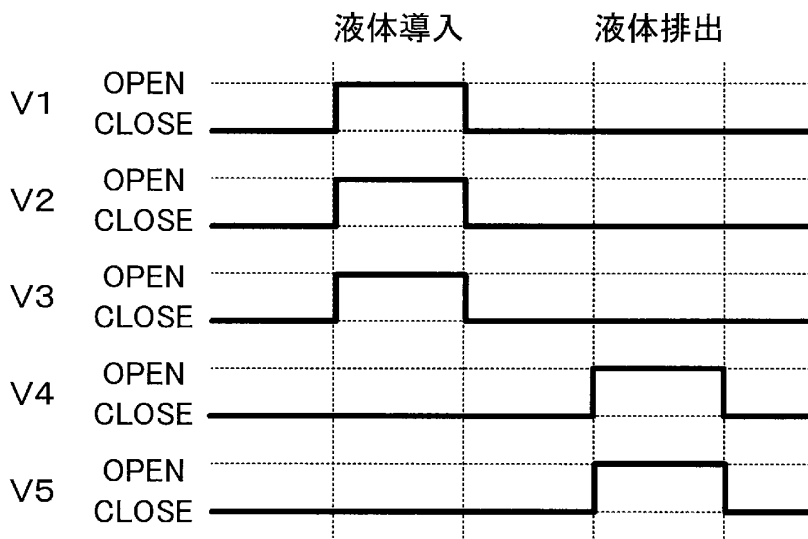


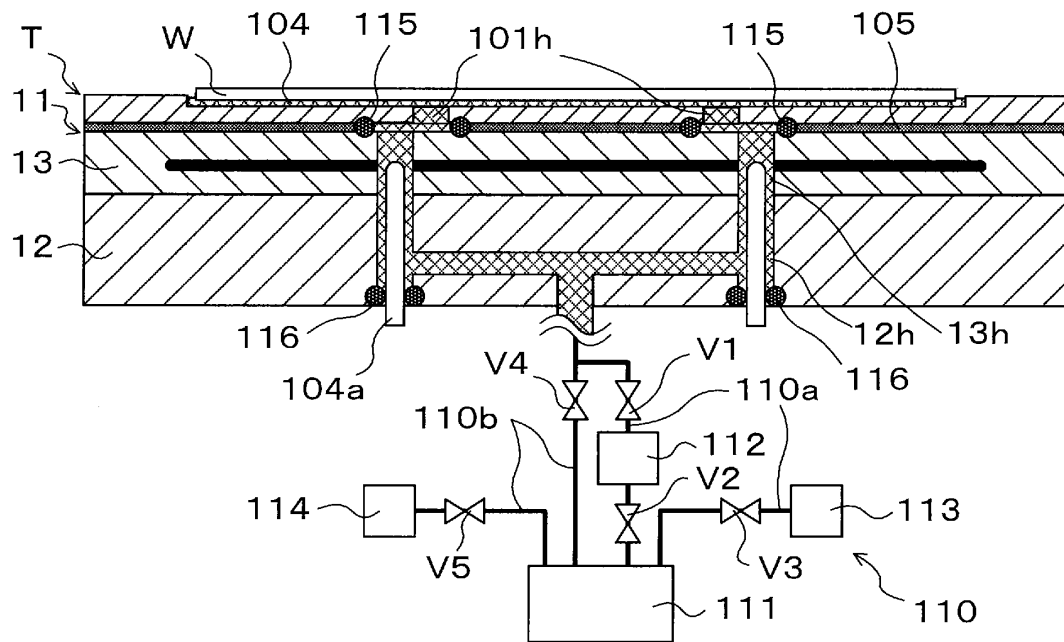
Figure 1 is a cross-sectional view of a device 11. The device 11 includes a substrate 12 and a layer 13. A thin layer 101 is disposed on top of the layer 13, and a thicker layer 108 is disposed on top of the thin layer 101. Two dark rectangular regions 102 are disposed on the left and right sides of the thin layer 101. A force T is applied to the left rectangular region 102. A series of square features are disposed on the substrate 12.

[illegible]

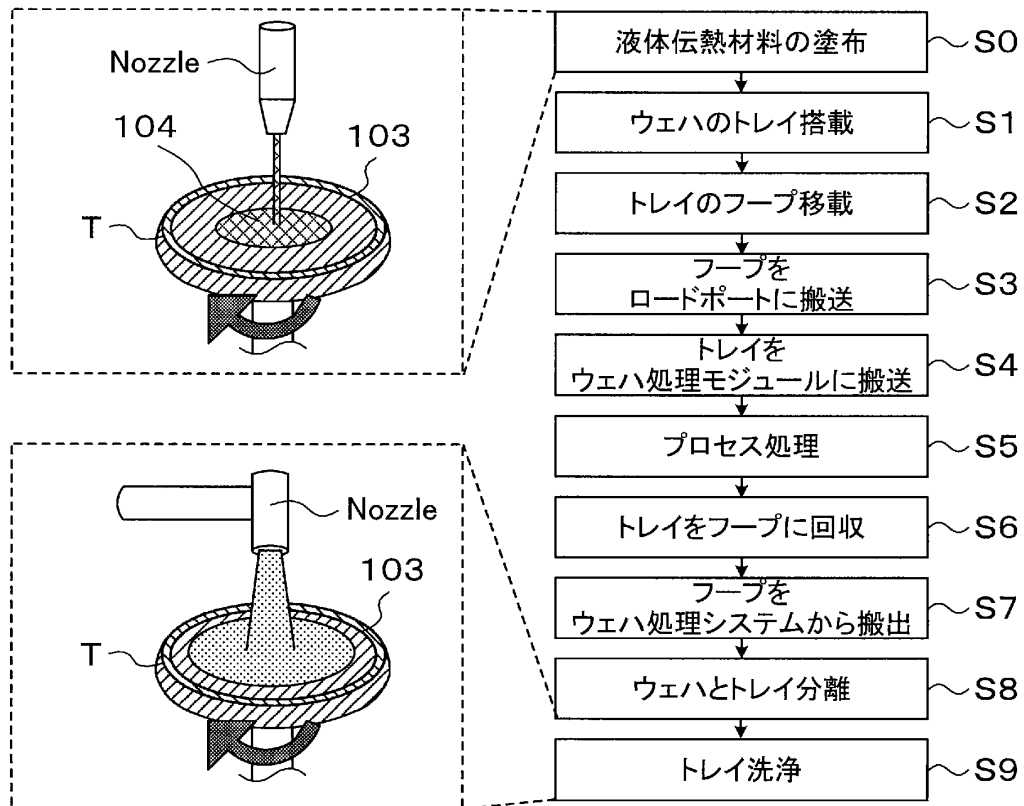
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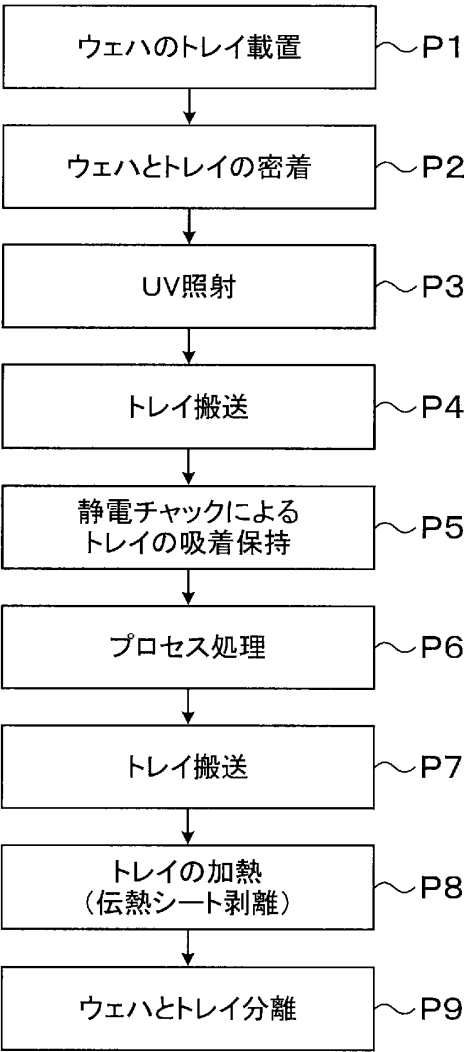
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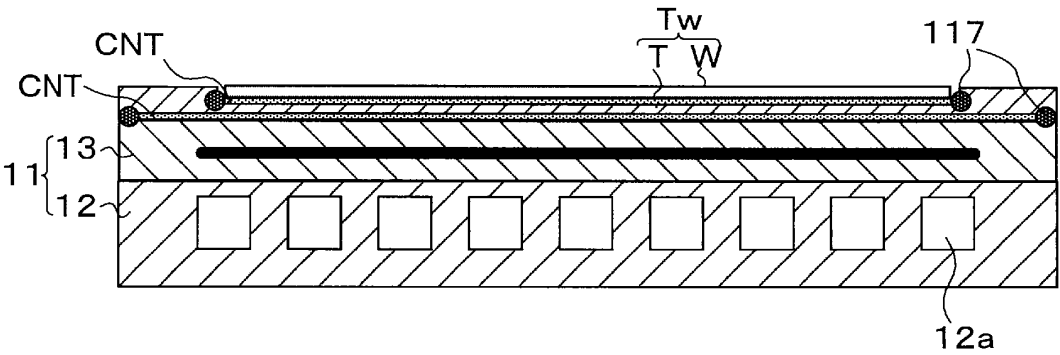
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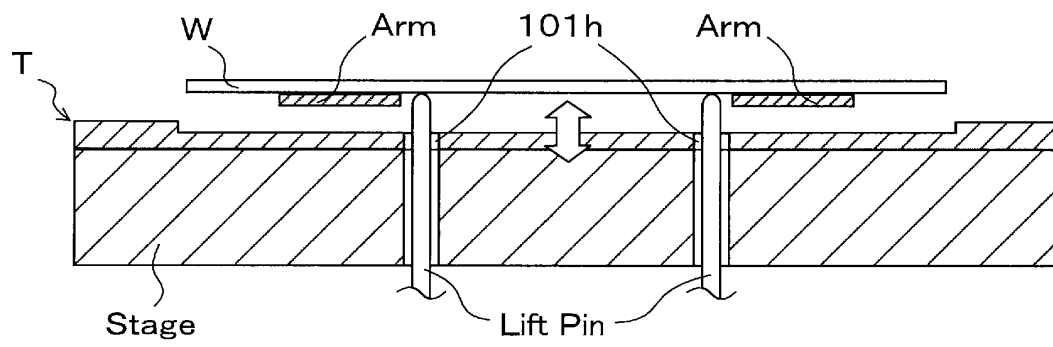
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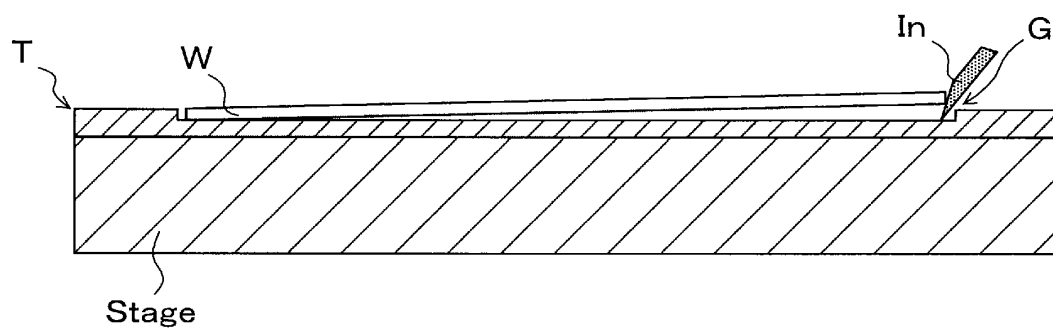
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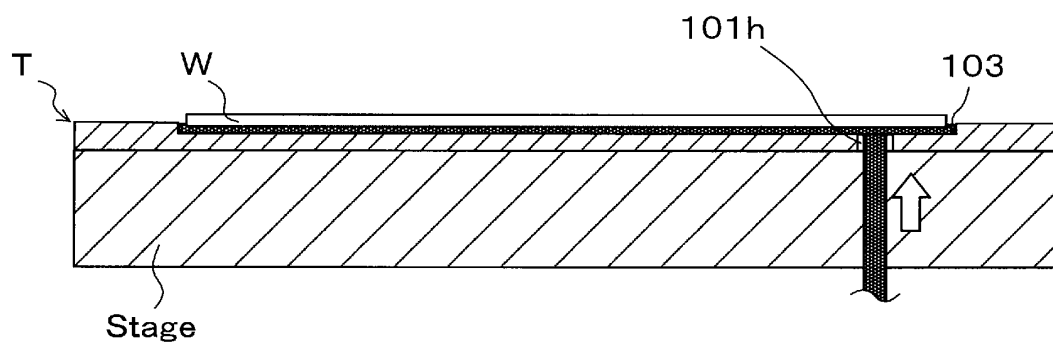
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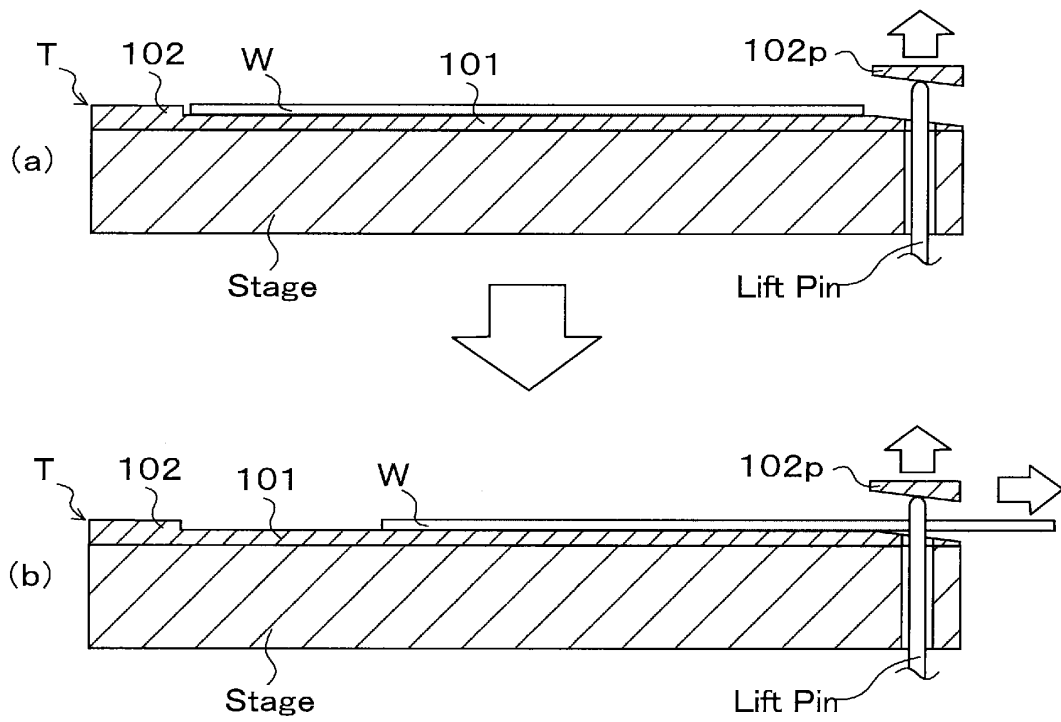
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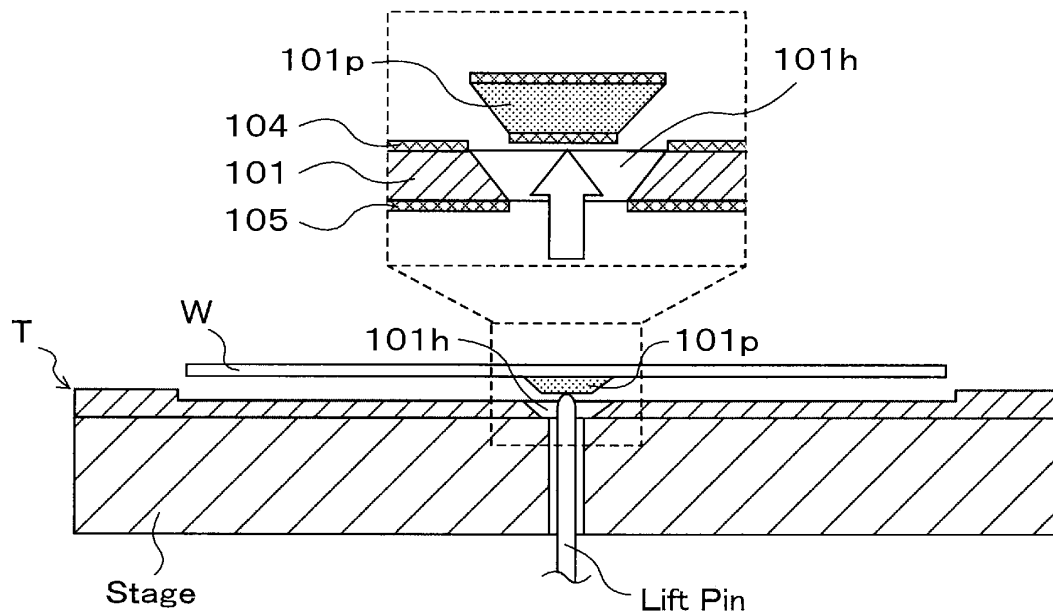
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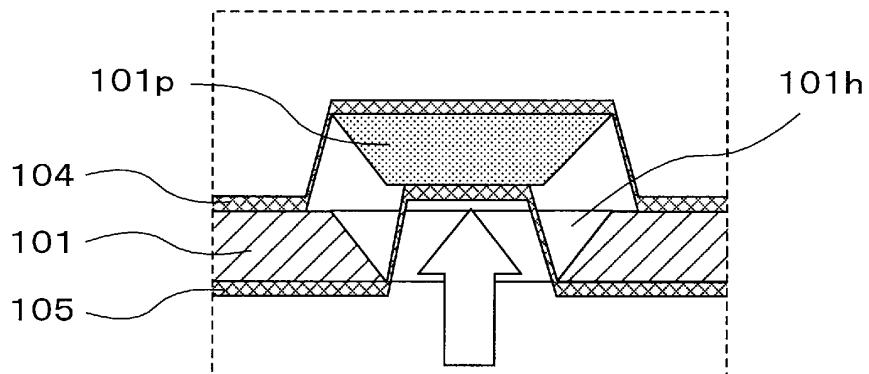
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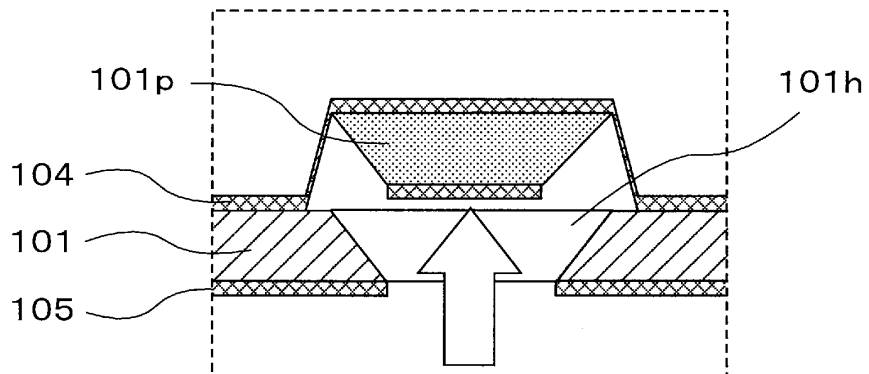
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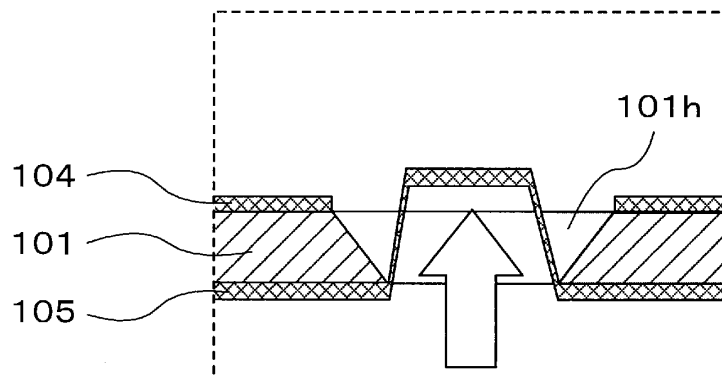
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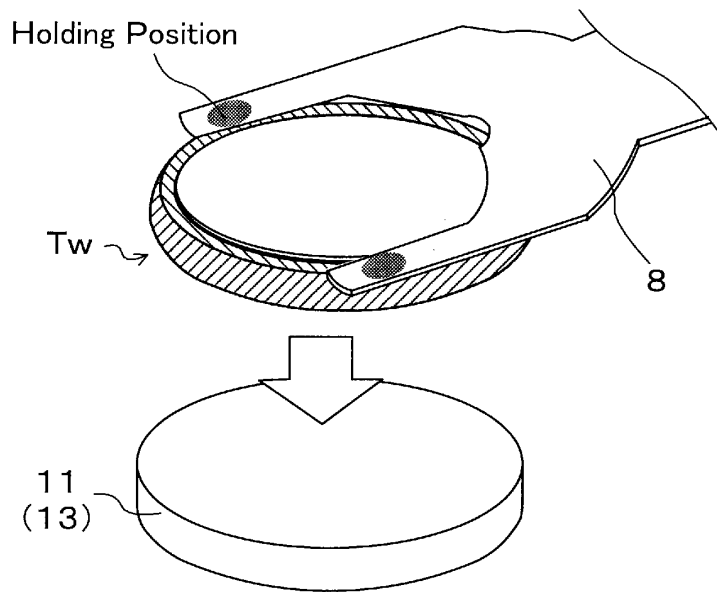
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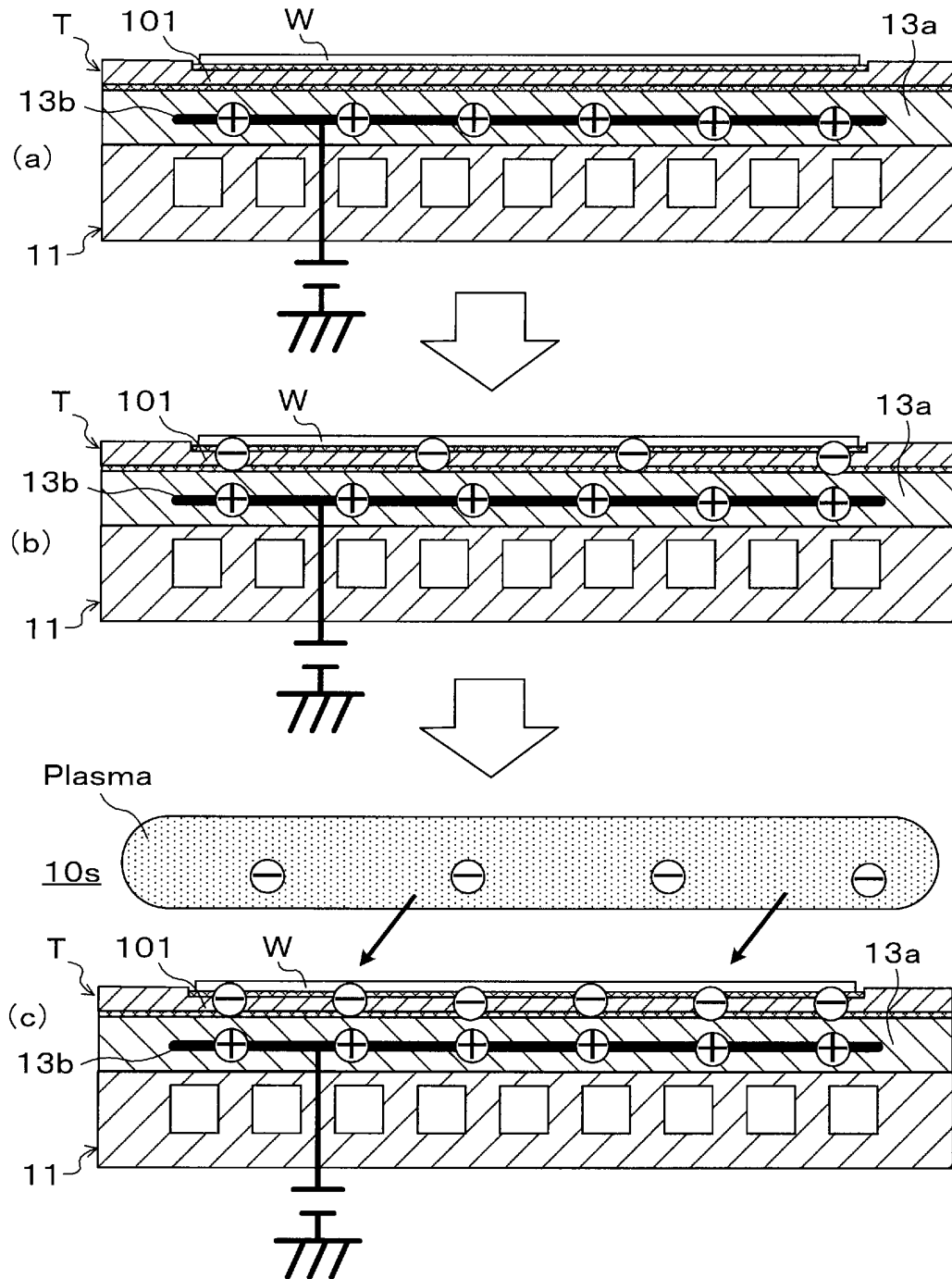
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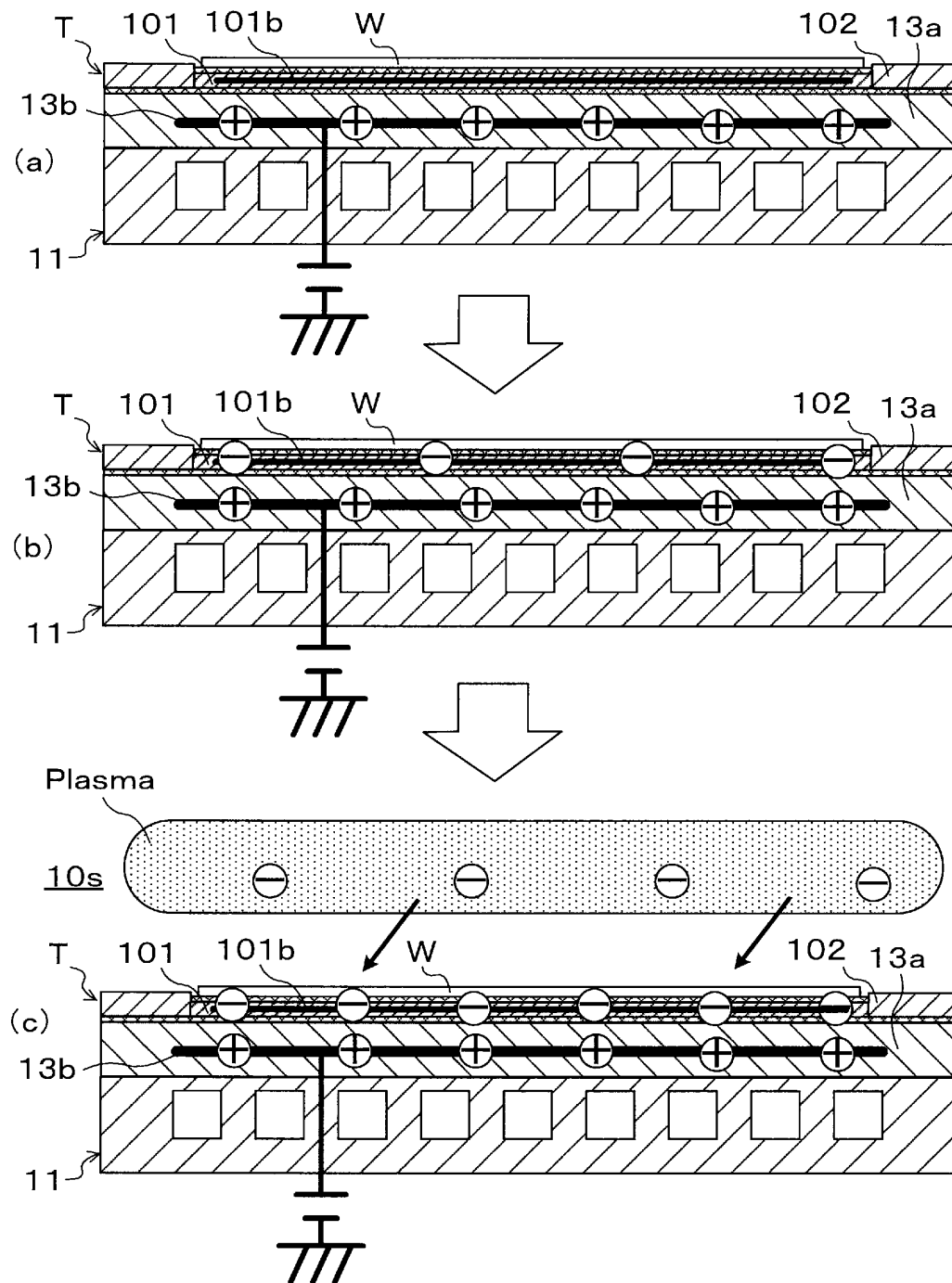
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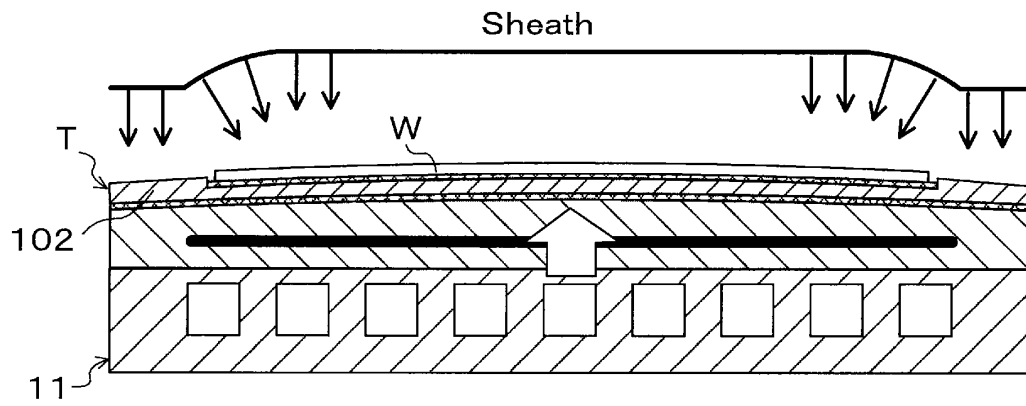
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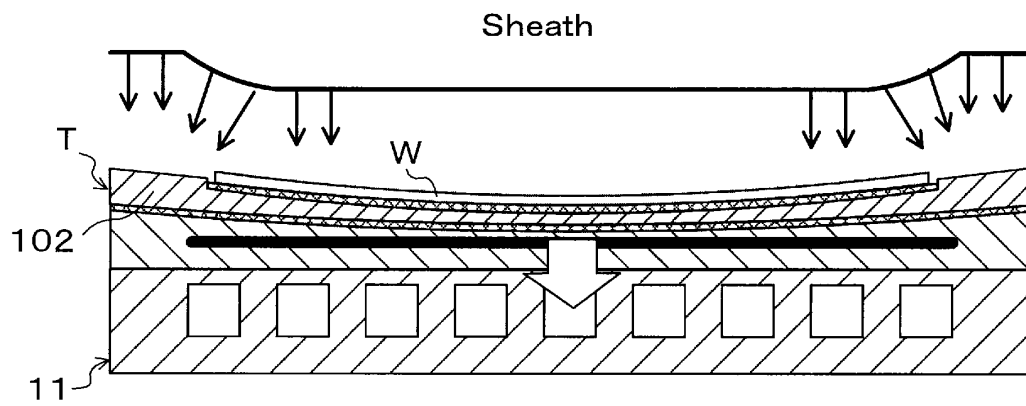
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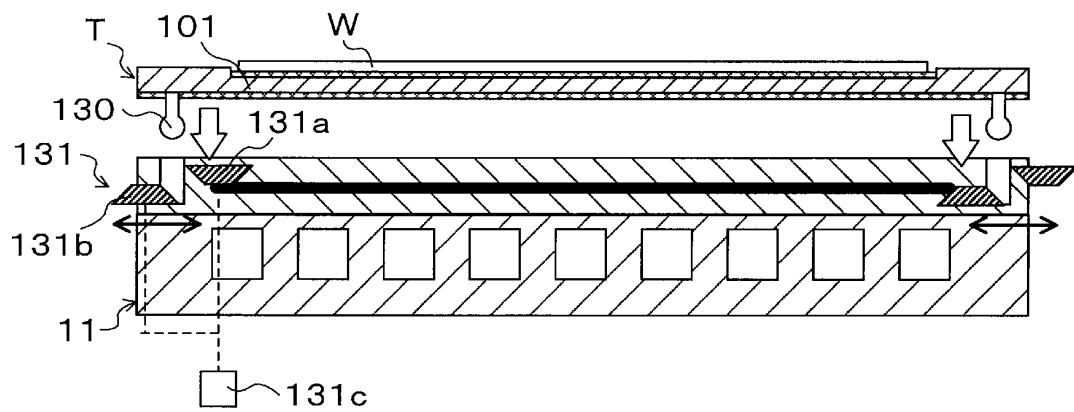
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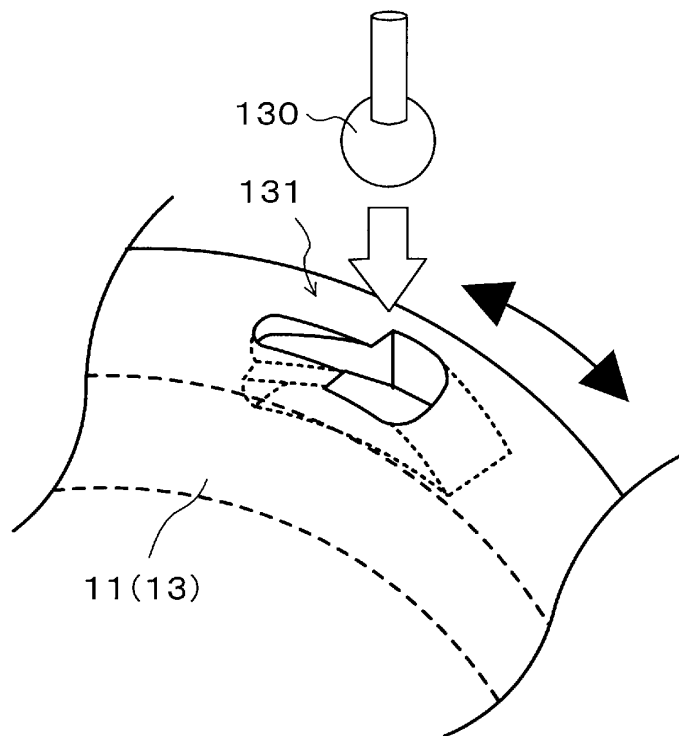
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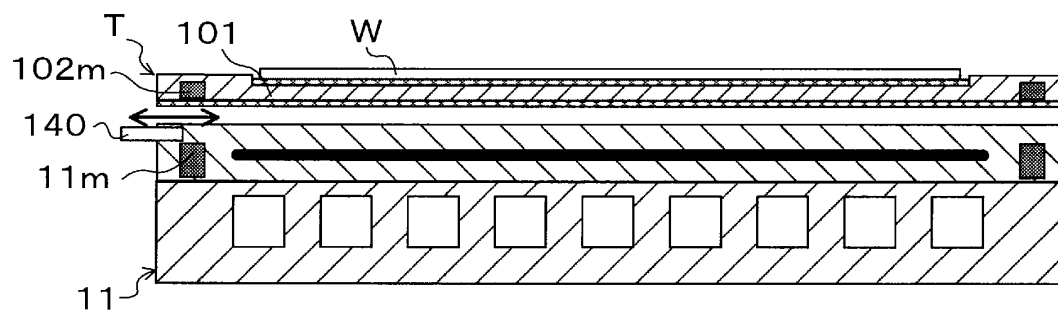
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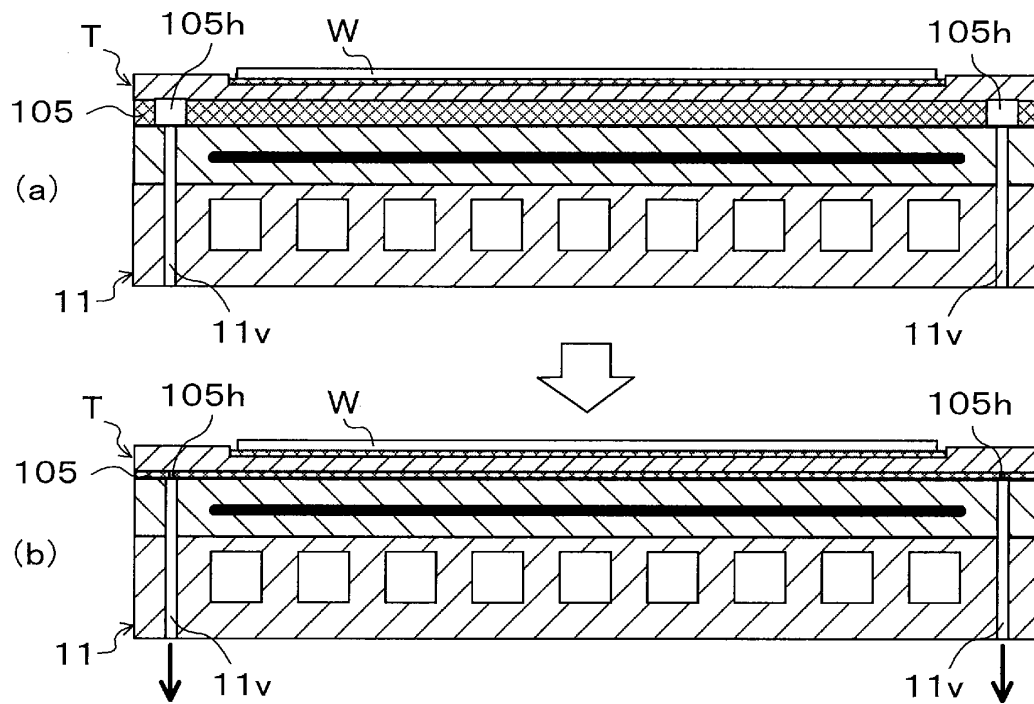
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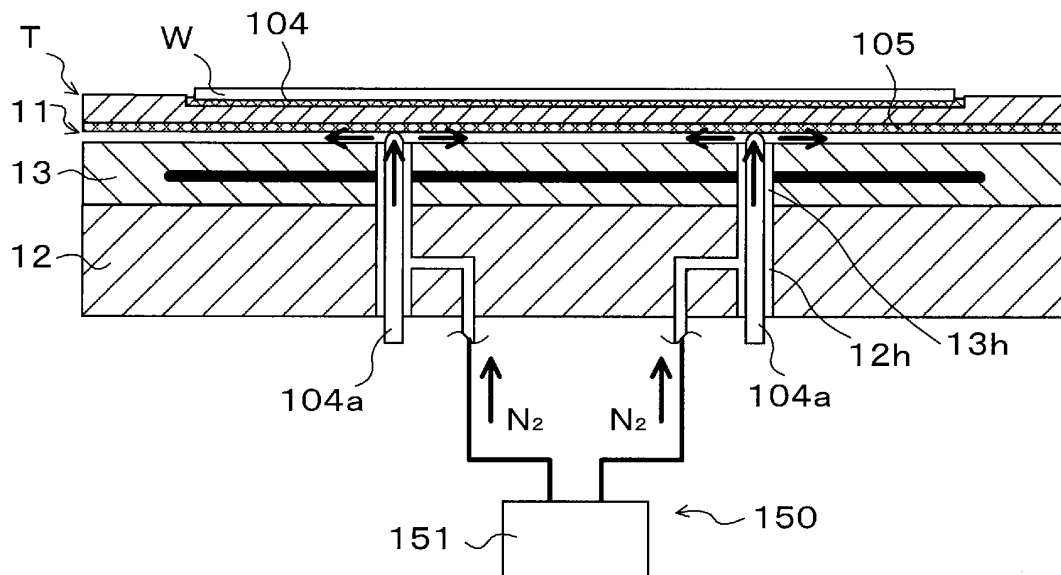
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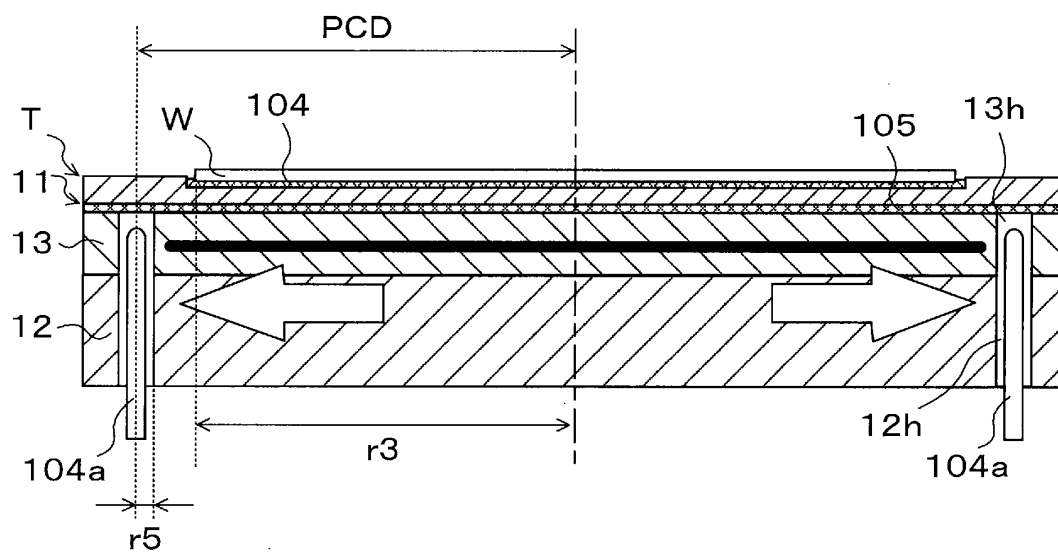
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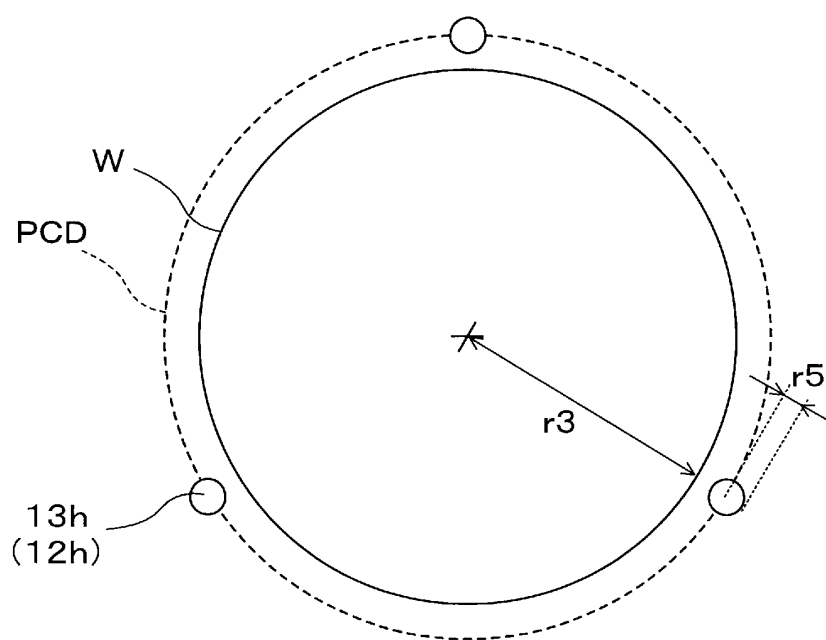
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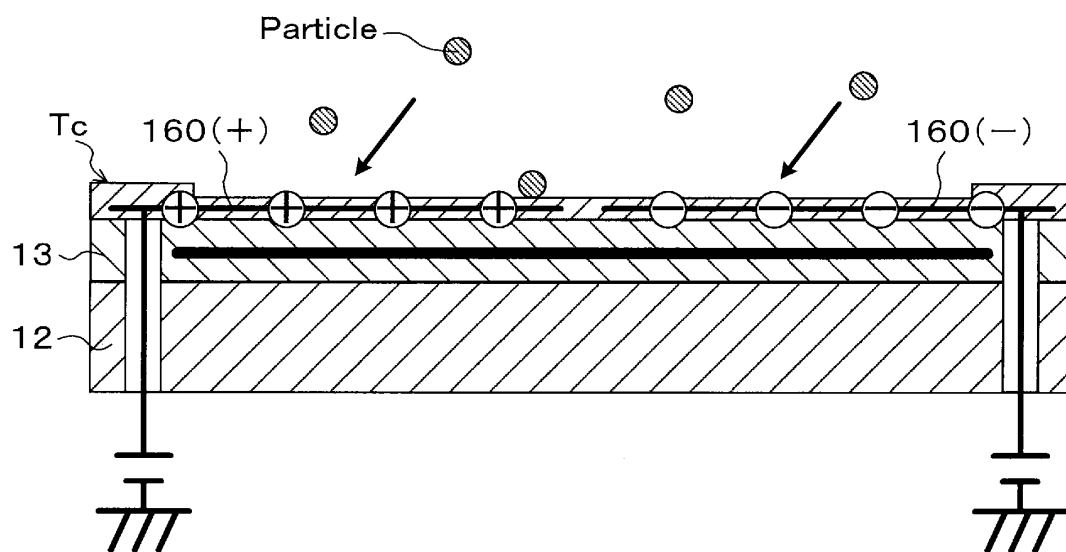
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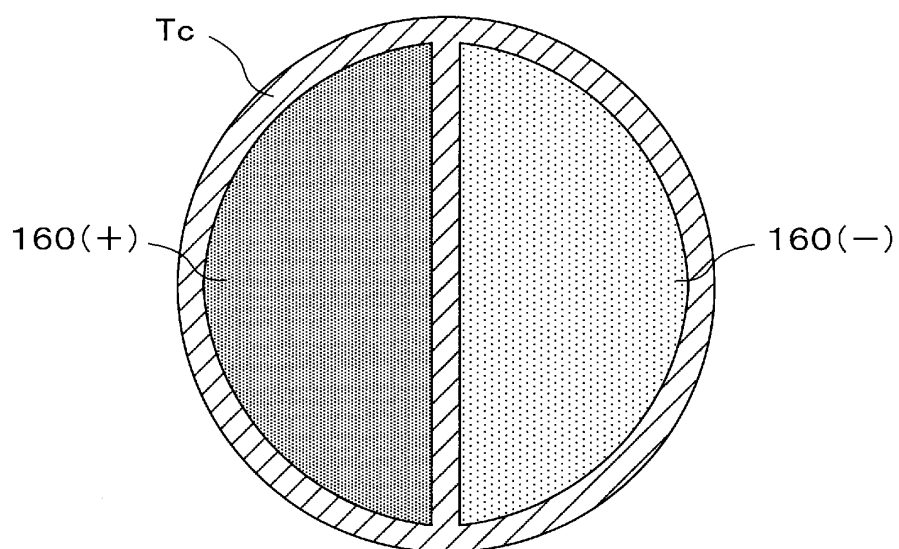
[図37]



[図38]



[図39]



[図40]

